Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Please cancel claims 1 and 8 without prejudice or disclaimer.

Please rewrite claims 2-7 and 9-20 as follows:

Listing of Claims:

1. (cancelled)

2. (currently amended) An epitaxial base substrate as defined in claim ~~1~~16, wherein said Group III nitride film includes at least 50 atomic ~~percentage~~ percent of elemental Al ~~element~~ for all of the Group III elements in the Periodic Table.

3. (currently amended) An epitaxial base substrate as defined in claim 2, wherein said Group III nitride film is made of AlN.

4. (currently amended) An epitaxial base substrate as defined in claim ~~1~~16, wherein said Group III nitride film is formed at a temperature of at least 1100°C by a MOCVD method.

5. (currently amended) An epitaxial base substrate as defined in claim 4, wherein said Group III nitride film is formed within a temperature range of 1100-1250°C.

6. (currently amended) An epitaxial base substrate as defined in claim ~~1~~16, wherein the elemental Al content of said Group III nitride film is continuously or stepwisely decreased in the thickness direction from said base toward the outside.

7. (currently amended) An epitaxial base substrate as defined in claim ~~1~~16, wherein the warpage of said epitaxial base substrate is reduced up to 50 μm.

8. (cancelled)

9. (currently amended) An epitaxial substrate as defined in claim ~~1~~17, wherein said Group III nitride buffer film includes at least 50 atomic ~~percentage~~ percent of elemental Al ~~element~~ for all of the Group III elements in the Periodic Table.

10. (currently amended) An epitaxial substrate as defined in claim 9, wherein said Group III nitride buffer film is made of AlN.

11. (currently amended) An epitaxial substrate as defined in claim ~~8~~17, wherein said Group III nitride buffer film is formed at a temperature of at least 1100°C by a MOCVD method.

12. (currently amended) An epitaxial substrate as defined in claim 11, wherein said Group III nitride buffer film is formed within a temperature range of 1100-1250°C.

13. (currently amended) An epitaxial substrate as defined in claim ~~8~~17, wherein said Group III nitride underfilm includes at least Ga element.

14. (currently amended) An epitaxial substrate as defined in claim 13, wherein the elemental Al content of said Group III nitride buffer film is continuously or stepwisely decreased in the thickness direction from said base toward said Group III nitride underfilm.

15. (currently amended) An epitaxial substrate as defined in claim ~~8~~17, wherein the warpage of said epitaxial substrate is reduced up to 50 μm.

16. (currently amended) An epitaxial base substrate ~~as defined in claim 1~~, comprising:

a base made of a single crystal material; and

a Group III nitride film including at least elemental Al and having a screw-type dislocation density up to $1\times10^{8}/cm^{2}$ formed on said base, wherein said Group III nitride film including at least elemental Al is formed directly on said base.

17. (currently amended) An epitaxial substrate ~~as defined in claim 8~~, comprising:

a base made of a single crystal material;

a Group III nitride buffer film including at least elemental Al and having a screw-type dislocation density up to $1\times10^{8}/cm^{2}$ formed on said base; and

a Group III nitride underfilm formed on said Group III nitride buffer film,

wherein said Group III nitride film including at least elemental Al is formed directly on said base.

18. (currently amended) An epitaxial base substrate as defined in claim ~~1~~16, wherein said screw-type dislocation density is less than $1\times10^{8}/cm^{2}$.

19. (currently amended) An epitaxial base substrate as defined in claim 18, wherein said screw-type dislocation density is up to $1\times10^{7}/cm^{2}$.

20. (currently amended) An epitaxial substrate as defined in claim ~~8~~17, wherein said screw-type dislocation density is less than $1\times10^{8}/cm^{2}$.

21. (previously presented) An epitaxial substrate as defined in claim 20, wherein said screw-type dislocation density is up to $1\times10^{7}/cm^{2}$.